

# SOT223 NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR

## FZT458

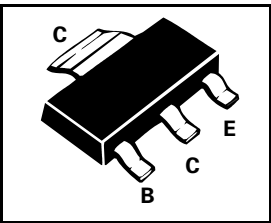
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### FEATURES

\* 400 Volt  $V_{CE0}$

COMPLEMENTARY TYPE – FZT558

PARTMARKING DETAIL – FZT458



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	400	V
Collector-Emitter Voltage	$V_{CEO}$	400	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Continuous Collector Current	$I_C$	300	mA
Peak Pulse Current	$I_{CM}$	1	A
Base Current	$I_B$	200	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	400		V	$I_C=100\mu A$
	$V_{CEO(sus)}$	400		V	$I_C=10mA^*$
	$V_{(BR)EBO}$	5		V	$I_E=100\mu A$
Collector Cut-Off Currents	$I_{CBO}$		100	nA	$V_{CB}=320V$
	$I_{CES}$		100	nA	$V_{CE}=320V$
Emitter Cut-Off Current	$I_{EBO}$		100	nA	$V_{EB}=4V$
Emitter Saturation Voltages	$V_{CE(sat)}$		0.2 0.5	V	$I_C=20mA, I_B=2mA^*$ $I_C=50mA, I_B=6mA^*$
	$V_{BE(sat)}$		0.9	V	$I_C=50mA, I_B=5mA^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		0.9	V	$I_C=50mA, V_{CE}=10V^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	300		$I_C=1mA, V_{CE}=10V$
		100			$I_C=50mA, V_{CE}=10V^*$
		15			$I_C=100mA, V_{CE}=10V^*$
Transition Frequency	$f_T$	50		MHz	$I_C=10mA, V_{CE}=20V$ $f=20MHz$
Collector-Base Breakdown Voltage	$C_{obo}$		5	pF	$V_{CB}=20V, f=1MHz$
Switching times	$t_{on}$		135 Typical	ns	$I_C=50mA, V_{CC}=100V$ $I_{B1}=5mA, I_{B2}=-10mA$
	$t_{off}$		2260 Typical	ns	

\*Measured under pulsed conditions. Pulse width=300 $\mu s$ . Duty cycle  $\leq 2\%$

Spice parameter data is available upon request for this device

For typical characteristics graphs see FMMT458 datasheet